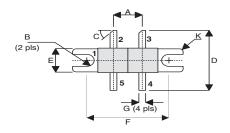
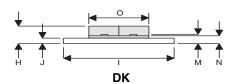


METAL GATE RF SILICON FET

MECHANICAL DATA





PIN 1 SOURCE (COMMON) PIN 2 DRAIN 1

PIN 3 DRAIN 2 PIN 4 GATE 2

PIN 5 GATE 1

DIM	mm	Tol.	Inches	Tol.
Α	6.45	0.13	0.254	0.005
В	1.65R	0.13	0.065R	0.005
С	45°	5°	45°	5°
D	16.51	0.76	0.650	0.03
Е	6.47	0.13	0.255	0.005
F	18.41	0.13	0.725	0.005
G	1.52	0.13	0.060	0.005
Н	4.82	0.25	0.190	0.010
1	24.76	0.13	0.975	0.005
J	1.52	0.13	0.060	0.005
K	0.81R	0.13	0.032R	0.005
M	0.13	0.02	0.005	0.001
N	2.16	0.13	0.085	0.005

GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 15W – 28V – 1GHz PUSH–PULL

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- VERY LOW C_{rss}
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN 13 dB MINIMUM

APPLICATIONS

 HF/VHF/UHF COMMUNICATIONS from DC to 2 GHz

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

$\overline{P_D}$	Power Dissipation	70W
BV_DSS	Drain – Source Breakdown Voltage *	65V
BV_{GSS}	Gate – Source Breakdown Voltage *	±20V
I _{D(sat)}	Drain Current *	3A
T _{stg}	Storage Temperature	−65 to 150°C
Tj	Maximum Operating Junction Temperature	200°C

^{*} Per Side

Semelab PIc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.



ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter		Test Conditions		Min.	Тур.	Max.	Unit
	PER SIDE						
BV _{DSS}	Drain-Source	V _{GS} = 0	I _D = 10mA	65			\ \
DVDSS	Breakdown Voltage	VGS = 0	ID = IOIIIA	05			\ \ \
I _{DSS}	Zero Gate Voltage	V 20V	V 0			3	m A
	Drain Current	$V_{DS} = 28V$	V _{GS} = 0			3	mA
I _{GSS}	Gate Leakage Current	V _{GS} = 20V	V _{DS} = 0			1	μΑ
V _{GS(th)}	Gate Threshold Voltage *	I _D = 10mA	$V_{DS} = V_{GS}$	1		7	V
9 _{fs}	Forward Transconductance *	V _{DS} = 10V	I _D = 0.6A	0.54			S
	TOTAL DEVICE						
G _{PS}	Common Source Power Gain	P _O = 15W		13			dB
η	Drain Efficiency	$V_{DS} = 28V$	$I_{DQ} = 0.6A$	40			%
VSWR	Load Mismatch Tolerance	f = 1GHz		20:1			_
PER SIDE							
C _{iss}	Input Capacitance	V _{DS} = 0	$V_{GS} = -5V$ f = 1MHz			36	pF
C _{oss}	Output Capacitance	V _{DS} = 28V	$V_{GS} = 0$ $f = 1MHz$			18	pF
C _{rss}	Reverse Transfer Capacitance	V _{DS} = 28V	$V_{GS} = 0$ $f = 1MHz$			1.5	pF

^{*} Pulse Test: Pulse Duration = 300 μs , Duty Cycle $\leq 2\%$

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 2.5°C / W
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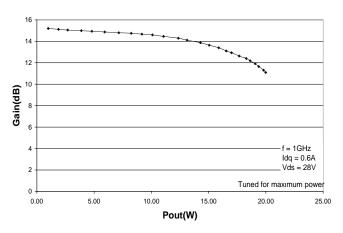
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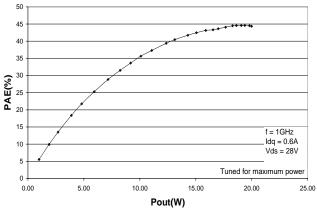
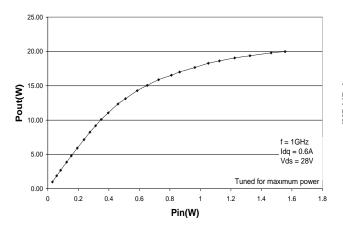


Figure 1
Gain vs. Output Power

Figure 2
Power Added Efficiency vs. Output Power



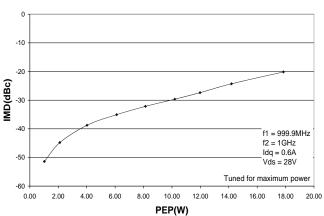
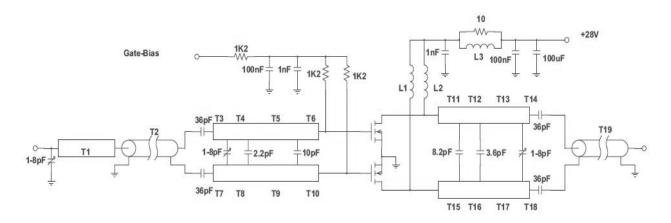


Figure 3
Output Power vs. Input Power

Figure 4 IMD3 vs. PEP

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1000MHz TEST FIXTURE

Substrate 0.8mm thick PTFE/glass All microstrip lines W = 2.7mm

11	23 mm
T2, T19	50mm 50 OHM UT 34 semi-rigid coax
T3, T7	6mm
T4, T8	8mm
T5, T9	15mm
T6, T10	9mm
T11,T15	8mm
T12,T16	7mm
T13,T17	11mm
T14,T18	5mm
L1,L2	6 turns of 24swg enamelled copper wire, 3mm i.d.

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1.5 turns of 24swg enamelled copper wire on Siemens B62152-a7x 2 hole core

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